OP165, OP166 Series



#### Features:

- T-1 (3 mm) package style
- Choice of narrow or wide irradiance pattern
- Choice of dome lens or flat lens
- Mechanically and spectrally matched to other OPTEK devices
- Higher power output than GaAs at equivalent drive currents
- 935 nm diode



#### Description:

Each device in the **OP165** and **OP166** series is a high intensity gallium arsenide infrared emitting diode (GaAIAs) that is molded in an IR transmissive clear epoxy package with either a dome or flat lens. Devices feature narrow and wide irradiance patterns and a variety of electrical characteristics. The small T-1 package style makes these devices ideal for space -limited applications.

OP165 and OP166 devices are mechanically and spectrally matched to the OP505 and OP535 series devices.

Please refer to Application Bulletins 208 and 210 for additional design information and reliability (degradation) data.

#### Applications:

- Space-limited applications
- Applications requiring coupling efficiency
- Battery-operated or voltage-limited applications

Ordering Information									
Part Number	LED Peak Wavelength	Output Power (mW/cm²) Min / Max	I <sub>F</sub> (mA) Typ / Max	Total Beam Angle	Lead Length				
OP165A	935 nm	1.95 / NA		18°	- 0.50"				
OP165B		1.40 / 2.20							
OP165C		0.85 / 1.60	20 / 50						
OP165D		0.28 / NA							
OP165W		0.50 / NA		90°					
OP166A		1.95 / NA		18°					
OP166B		1.40 / 2.20							
OP166C		0.85 / 1.60							
OP166D		0.28 / NA							
OP166W		0.50 / NA		90°					



OP165, OP166 Series

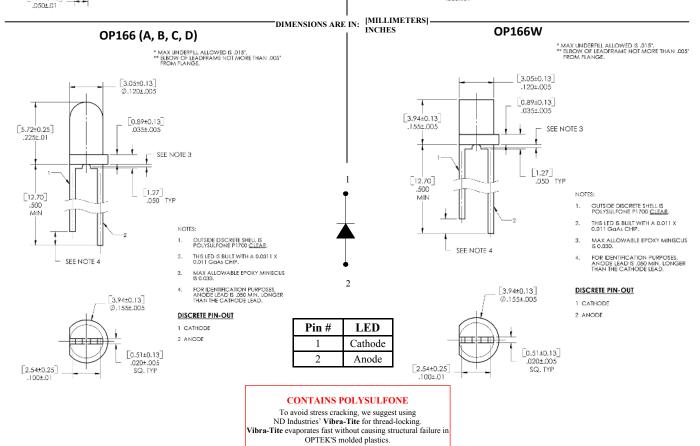


### OP165 (A, B, C, D) [5.72±0.25] [0.89±0.13] .035±.005 SEE NOTE 3 MAX UNDERFILL ALLOWED IS .015". [17.15±0] .675±.000 OUTSIDE DISCRETE SHELL IS POLYSULFONE P1700 CLEAR. THIS LED IS BUILT WITH A 0.0011 X 0.011 GgAs CHP. FOR IDENTIFICATION PURPOSES, ANODE LEAD IS .065 ± .035 LONGER THAN THE CATHODE LEAD. L SEE NOTE 4 DISCRETE PIN-OUT [3.94±0.13] Ø.155±.005 1 CATHODE 2 ANODE Ш 0.51±0.13 [1.27±0.25]

### **OP165W** [3.05±0.13] 3.94±0.13 0.89±0.13 .035±.005 SEE NOTE 3 " MAX UNDERFILL ALLOWED IS .015". [17.15±0.64] .675±.025 OUTSIDE DISCRETE SHELL IS POLYSULFONE P1700 CLEAR. THIS LED IS BUILT WITH A 0.011 X 0.011 GaAs CHIP. MAX ALLOWABLE EPOXY MINISCUS IS 0.030. FOR IDENTIFICATION PURPOSES, ANODE LEAD IS .065 ± .035 LONGER THAN THE CATHODE LEAD. SEE NOTE 4 [3.94±0.13] Ø.155±.005 DISCRETE PIN-OUT 1 CATHODE Ш [0.51±0.13]

.020±.005 SQ. TYP

[1.27±0.25] .050±.01



OP165, OP166 Series



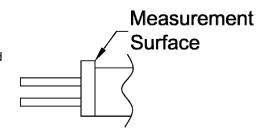
## **Electrical Specifications**

Absolute Maximum Ratings (T <sub>A</sub> = 25° C unless otherwise noted)				
Storage and Operating Temperature Range	-40° C to +100° C			
Reverse Voltage	2.0 V			
Continuous Forward Current	50 mA			
Peak Forward Current (1 µs pulse width, 300 pps)	3.0 A			
Lead Soldering Temperature [1/16 inch (1.6 mm) from case for 5 seconds with soldering iron]	260° C			
Power Dissipation	100 mW <sup>(1)</sup>			

Electrical Characteristics (T <sub>A</sub> = 25° C unless otherwise noted)								
SYMBOL	PARAMETER		TYP	MAX	UNITS	TEST CONDITIONS		
Input Diode								
E <sub>E (APT)</sub>	Apertured Radiant Incidence OP165A, OP166A		-	-	mW/cm²	I <sub>F</sub> = 20 mA <sup>(2)</sup>		
Po	Radiant Power Output OP165W, OP166W	0.50	-	-	mW	I <sub>F</sub> = 20 mA		
V <sub>F</sub>	Forward Voltage	-	-	1.60	V	I <sub>F</sub> = 20 mA		
$I_{R}$	Reverse Current	-	-	100	μA	V <sub>R</sub> = 2 V		
$\lambda_{P}$	Wavelength at Peak Emission	-	935	-	nm	I <sub>F</sub> = 10 mA		
В	Spectral Bandwidth between Half Power Points	-	50	-	nm	I <sub>F</sub> = 10 mA		
$\Delta\lambda_{\scriptscriptstyle P}/\Delta T$	Spectral Shift with Temperature OP165, OP166 (A, B, C, D) OP165W, OP166W	- -	- ±0.30	- -	nm/°C	I <sub>F</sub> = Constant		
$\theta_{HP}$	Emission Angle at Half Power Points OP165, OP166 (A, B, C, D) OP165W, OP166W		18 90		Degree	I <sub>F</sub> = 20 mA		
t <sub>r</sub>	Output Rise Time	-	1000	-	ns	- I <sub>F(PK)</sub> =100 mA, PW=10 μs, D.C.=10.0 %		
t <sub>f</sub>	Output Fall Time	-	500	-	ns			

#### Notes:

- 1. Derate linearly 1.33 mW/°C above 25°C
- 2.  $E_{E(APT)}$  is a measurement of the average apertured rediant incidence ipon a sensing area 0.081" (2.06 mm) in diameter, perpendicular to and centered on the mechanical axis of the lens, and 0.590" (14.99 mm) from the measurement surface.  $E_{E(APT)}$  is not necessarily uniform within the measured areas.

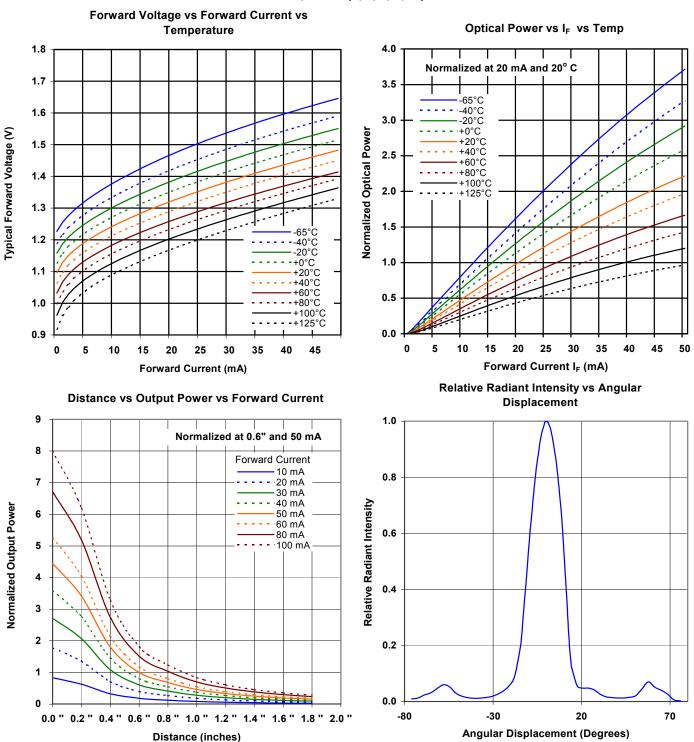


OP165, OP166 Series



### Performance

OP165, OP166 (A, B, C, D, W)



General Note

TT Electronics reserves the right to make changes in product specification without notice or liability. All information is subject to TT Electronics' own data and is considered accurate at time of going to print.

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